L Number	Hits	Search Text	DB	Time stamp
-	23781	guard$3 near1 ring or metal near ring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:02
-	18657	trench same (conductive near material or metal or polysilicon or silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:06
-	180043	interconnection near layer$1 or metal near layer$1 or polysilicon near layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:07
-	688503	passive or inductor$1 or capacitor$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:08
-	1790062	active or transistor$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:08
-	1602	(trench same (conductive near material or metal or polysilicon or silicide)) same (encircle or surround$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:09
-	27	(guard$3 near1 ring or metal near ring) and ((trench same (conductive near material or metal or polysilicon or silicide)) same (encircle or surround$3)) and (interconnection near layer$1 or metal near layer$1 or polysilicon near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:10
-	22	((guard$3 near1 ring or metal near ring) and ((trench same (conductive near material or metal or polysilicon or silicide)) same (encircle or surround$3)) and (interconnection near layer$1 or metal near layer$1 or polysilicon near layer)) and @ad<=20010418	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:28
-	21	(((guard$3 near1 ring or metal near ring) and ((trench same (conductive near material or metal or polysilicon or silicide)) same (encircle or surround$3)) and (interconnection near layer$1 or metal near layer$1 or polysilicon near layer)) and @ad<=20010418) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 09:28